DMJ70H1D3SJ3

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
700V	1.3Ω @ V_{GS} = 10V	4.6A

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

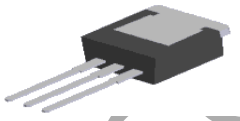
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

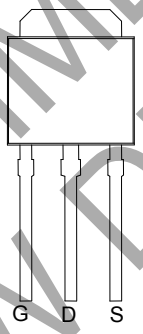
Mechanical Data

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

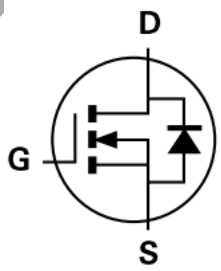
TO251
Top View



TO251
Bottom View



Top View
Pin Configuration



Internal Schematic

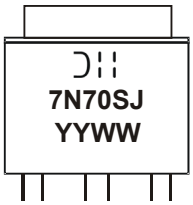
Ordering Information (Note 4)

Part Number	Case	Packaging
DMJ70H1D3SJ3	TO251	75 Pieces/Tube

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

TO251



=Manufacturer's Marking
7N70SJ = Product Type Marking Code
YYWW = Date Code Marking
YY or YY= Last Digit of Year (ex: 16 = 2016)
WW or WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current (Note 5) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	4.6 2.9	A
Maximum Body Diode Forward Current (Note 6)		I_S	3.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	5.4	A
Avalanche Current (Note 7)	L = 60mH	I_{AS}	1.1	A
Avalanche Energy (Note 7)	L = 60mH	E_{AS}	40	mJ
Peak Diode Recovery dv/dt (Note 7)		dv/dt	5	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	41	W
	T_C = +100°C		16	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\Theta JA}$	79	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{\Theta JC}$	3.0	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	700	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 700V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	100	nA	V_{GS} = ±30V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	2.9	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.0	1.3	Ω	V_{GS} = 10V, I_D = 2.5A
Diode Forward Voltage	V_{SD}	—	0.9	1.3	V	V_{GS} = 0V, I_S = 5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{ISS}	—	351	—	pF	V_{DS} = 50V, f = 1MHz, V_{GS} = 0V
Output Capacitance	C_{OSS}	—	66	—		
Reverse Transfer Capacitance	C_{RSS}	—	1.1	—		
Gate Resistance	R_G	—	3.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_G	—	13.9	—	nC	V_{DD} = 560V, I_D = 5A, V_{GS} = 10V
Gate-Source Charge	Q_{GS}	—	1.9	—		
Gate-Drain Charge	Q_{GD}	—	8.5	—		
Turn-On Delay Time	$t_{D(ON)}$	—	8.5	—	ns	V_{DD} = 350V, V_{GS} = 10V, R_G = 4.7Ω, I_D = 2.5A
Turn-On Rise Time	t_R	—	11.6	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	24.5	—		
Turn-Off Fall Time	t_F	—	10	—		
Body Diode Reverse Recovery Time	t_{RR}	—	212	—	ns	I_S = 5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Time (T_J = +150°C)	t_{RR}	—	251	—	ns	
Body Diode Reverse Recovery Charge	Q_{RR}	—	1.8	—	µC	
Body Diode Reverse Recovery Charge (T_J = +150°C)	Q_{RR}	—	2.3	—	µC	

Notes:
5. Device mounted on infinite heatsink.
6. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
7. Guaranteed by design. Not subject to production testing.
8. Short duration pulse test used to minimize self-heating effect.

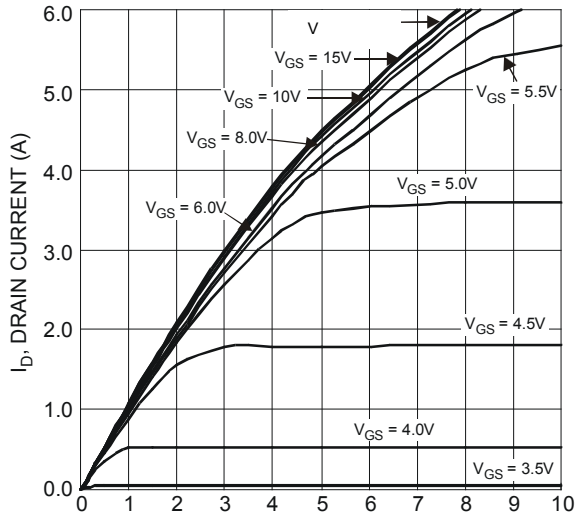


Figure 1 Typical Output Characteristics

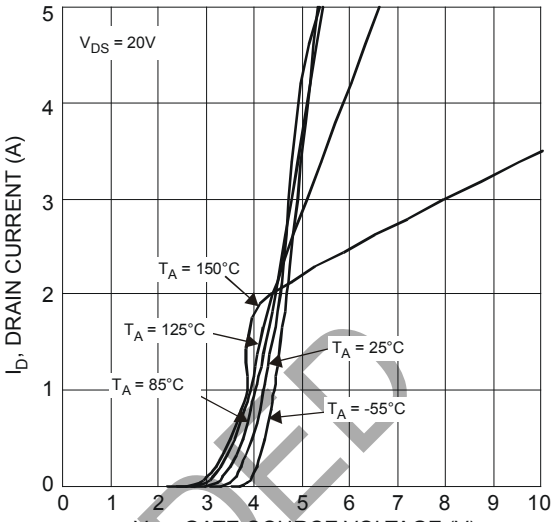


Figure 2 Typical Transfer Characteristics

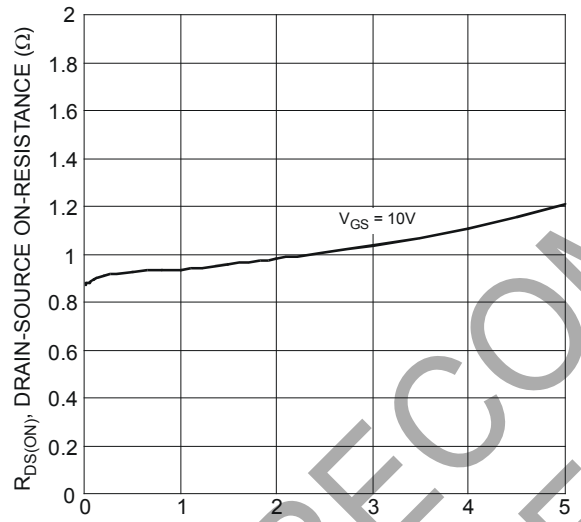


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

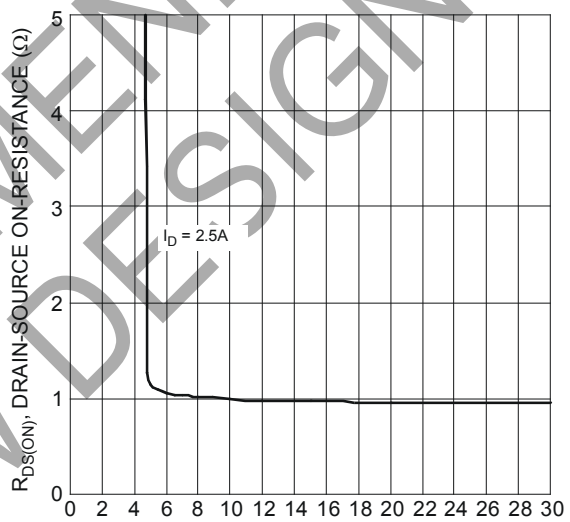


Figure 4 Typical Transfer Characteristics

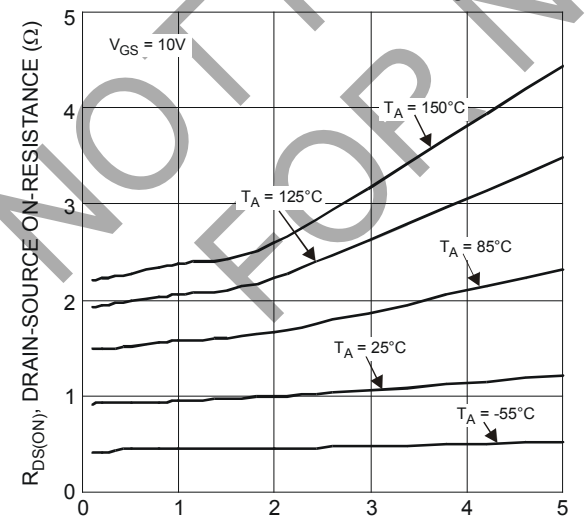


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

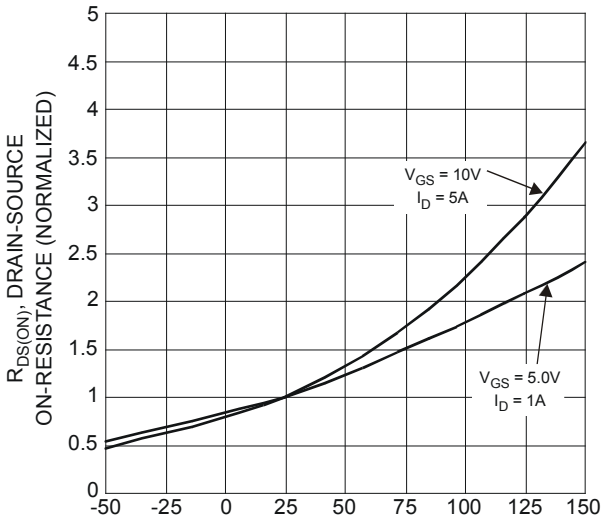


Figure 6 On-Resistance Variation with Temperature

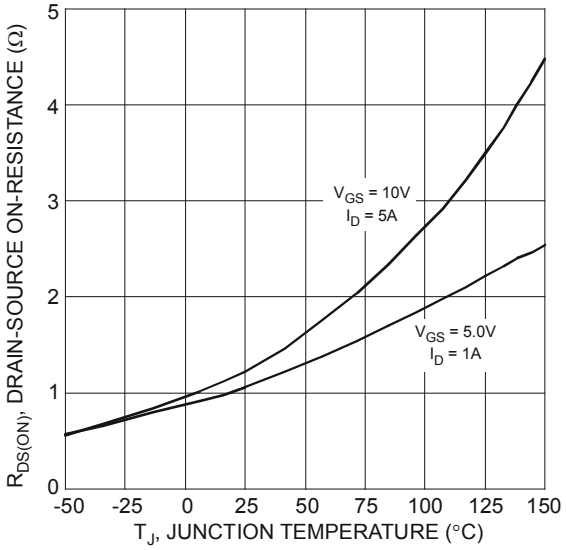


Figure 7 On-Resistance Variation with Temperature

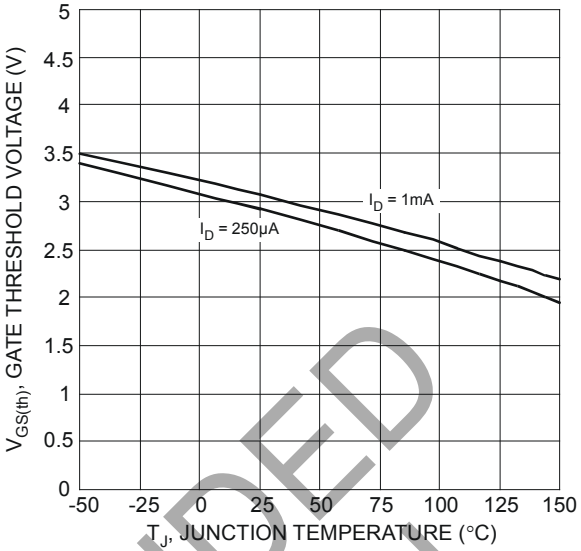


Figure 8 Gate Threshold Variation vs. Ambient Temperature

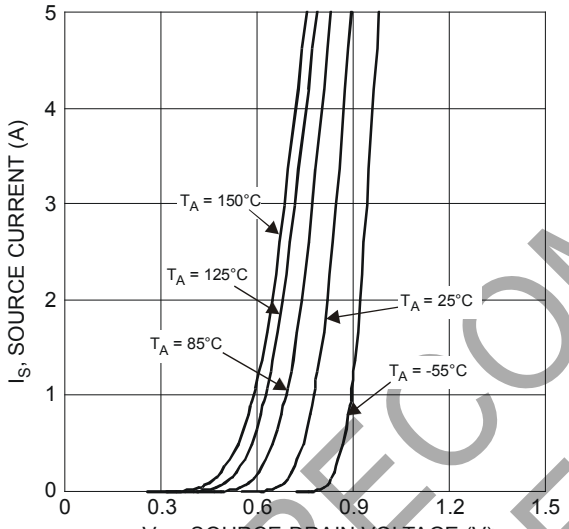


Figure 9 Diode Forward Voltage vs. Current

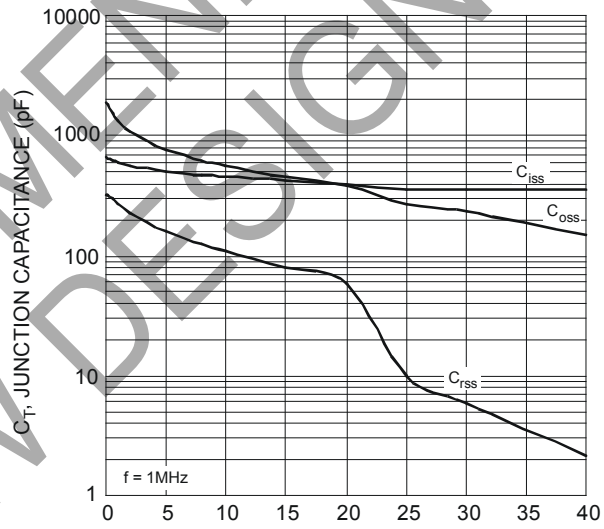


Figure 10 Typical Junction Capacitance

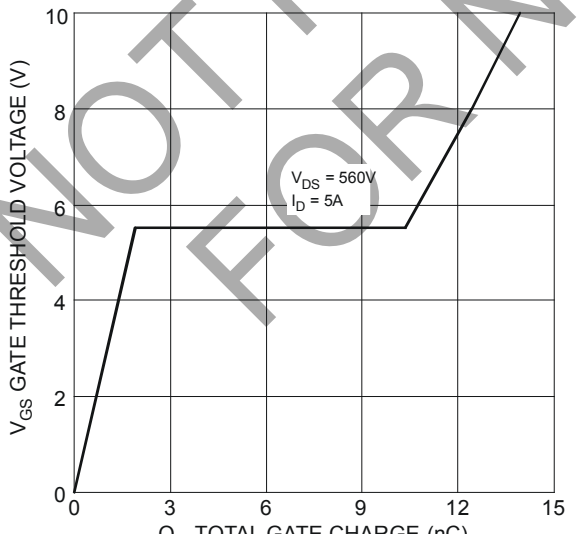


Figure 11 Gate Charge

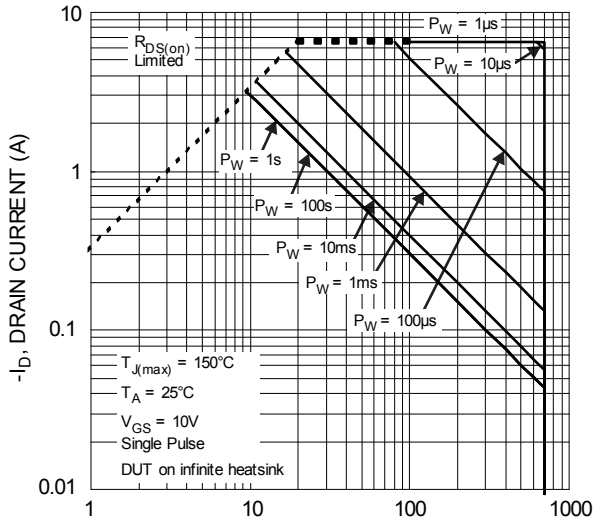


Figure 12 SOA, Safe Operation Area

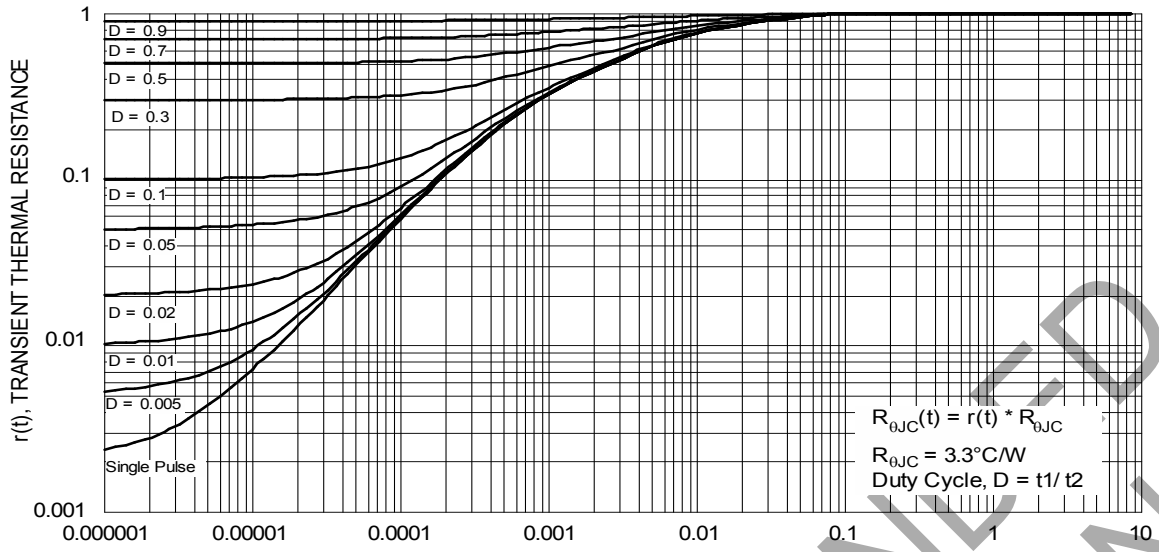
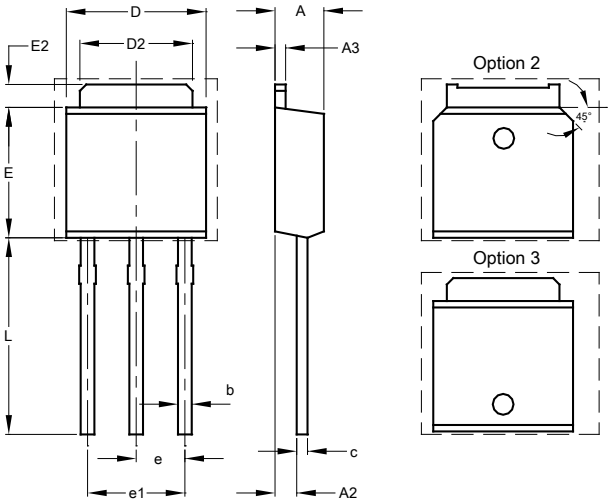


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

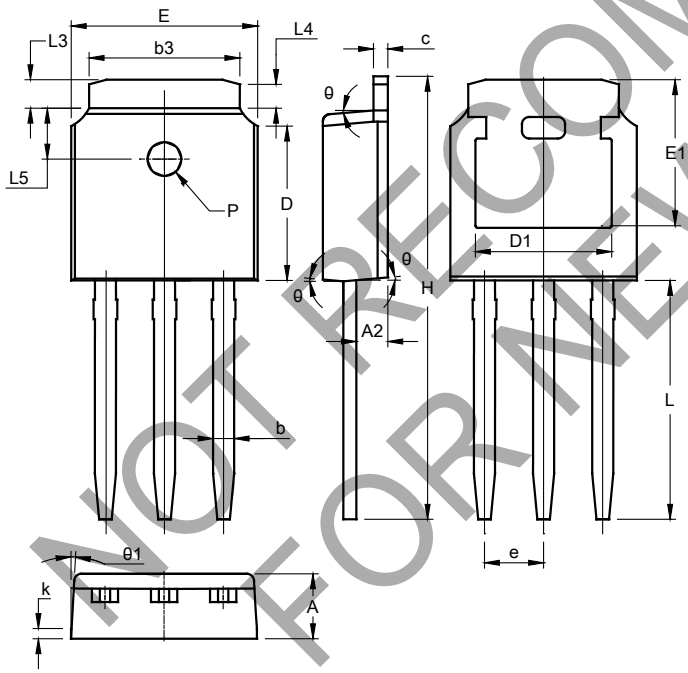
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

TO251



TO251		
Dim	**Min**	**Max**
A	2.200	2.400
A2	0.890	1.150
A3	0.450	0.550
B	0.550	0.740
C	0.450	0.570
D	6.400	6.750
D2	5.200	5.400
E	5.950	6.250
E2	0.900	1.250
E	2.240	2.340
e1	4.430	4.730
L	8.900	9.500
All Dimensions in mm		

TO251 (Type TH)



TO251 (Type TH)			
Dim	**Min**	**Max**	**Typ**
A	2.20	2.40	2.30
A2	0.97	1.17	1.07
b	0.68	0.90	0.78
b3	5.20	5.50	5.33
c	0.43	0.63	0.53
D	5.98	6.22	6.10
D1	5.30 REF		
e	2.286 BSC		
E	6.40	6.80	6.60
E1	4.63	5.03	4.83
H	16.22	16.82	16.52
k	0.40REF		
L	9.15	9.65	9.40
L3	0.88	1.28	1.02
L4	0.75 REF		
L5	1.65	1.95	1.80
PØ	1.20		
θ	5°	9°	7°
θ1	5°	9°	7°
All Dimensions in mm			

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